

Substitute for Form 1449A/PTO (Modified)						Complete if Known					
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>						Application Number		10/652,350			
						Filing Date		August 29, 2003			
						First Named Inventor:		John Barnak			
						Group Art Unit		2818			
						Examiner Name		Dao H. Nguyen			
Sheet		1		of		1		Attorney Docket Number		42P15042	
U.S. PATENT DOCUMENTS											
Exam. Initial*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear					
		Number Code ²	Kind (If known)								
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Exam. Initial*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²			
		Office ³	Number ⁴	Kind Code ⁵ (If known)							
OTHER ART - NON PATENT LITERATURE DOCUMENTS											
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published							T ²		
dhu		EUROPEAN PATENT OFFICE, International Search Report and Written Opinion for International Application No. PCT/US2004/026893, 15 pages, December 14, 2004.									
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Examiner Signature	Date Considered							06/20/05			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard S.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.